



- (51) International Patent Classification:
H01L 21/20 (2006.01) *H01L 21/02* (2006.01)
- (21) International Application Number:
PCT/US2015/048167
- (22) International Filing Date:
2 September 2015 (02.09.2015)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
- | | | |
|------------|-------------------------------|----|
| 62/046,559 | 5 September 2014 (05.09.2014) | US |
| 62/046,400 | 5 September 2014 (05.09.2014) | US |
| 62/046,377 | 5 September 2014 (05.09.2014) | US |
| 62/046,414 | 5 September 2014 (05.09.2014) | US |
| 62/046,451 | 5 September 2014 (05.09.2014) | US |
| 14/584,441 | 29 December 2014 (29.12.2014) | US |
| 14/826,065 | 13 August 2015 (13.08.2015) | US |
| 14/826,310 | 14 August 2015 (14.08.2015) | US |
| 14/826,287 | 14 August 2015 (14.08.2015) | US |
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(54) Title: ATMOSPHERIC EPITAXIAL DEPOSITION CHAMBER

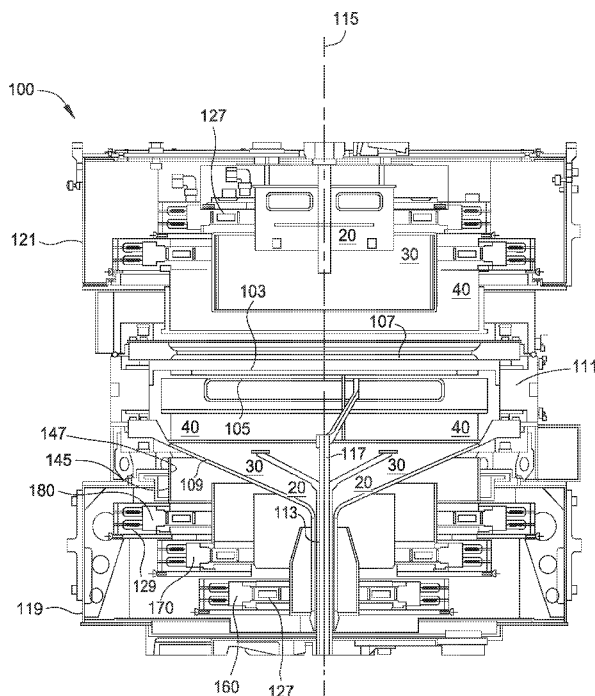


FIG. 1

(57) Abstract: Embodiments described herein disclose epitaxial deposition chambers and components thereof. In one embodiment, a chamber can include a substrate support positioned in a processing region, a radiant energy assembly comprising a plurality of radiant energy sources, a liner assembly having an upper liner and a lower liner, and a dome assembly positioned between the substrate support and the radiant energy assembly. The epitaxial deposition chambers described herein allow for processing of larger substrates, while maintaining throughput, reducing costs and providing a reliably uniform deposition product.



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(81) **Designated States** (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JP, KE, KG, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) **Designated States** (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))